











SN74HCS4075

SCLS795A - FEBRUARY 2020 - REVISED JUNE 2020

SN74HCS4075 Triple 3-Input OR Gates with Schmitt-Trigger Inputs

Features

- Wide operating voltage range: 2 V to 6 V
- Schmitt-trigger inputs allow for slow or noisy input signals
- Low power consumption
 - Typical I_{CC} of 100 nA
 - Typical input leakage current of ±100 nA
- ±7.8-mA output drive at 5 V
- Extended ambient temperature range: -40°C to +125°C, TA

Applications

- User fewer inputs to monitor error signals
- Combine active-low enable signals

Description

This device contains three independent 3-input OR Gates with Schmitt-trigger inputs. Each gate performs the Boolean function Y = A + B + C in positive logic.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)		
SN74HCS4075DR	SOIC (14)	8.70 mm × 3.90 mm		
SN74HCS4075PWR	TSSOP (14)	5.00 mm × 4.40 mm		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Benefits of Schmitt-trigger Inputs

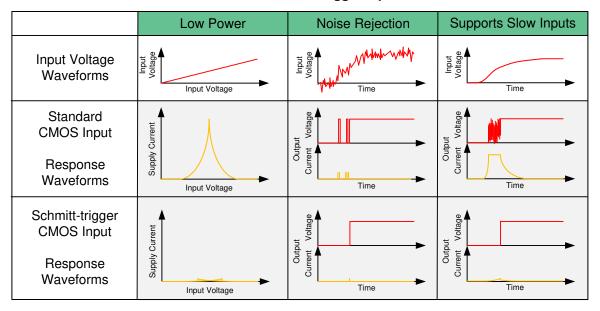




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4 Revision History

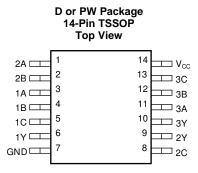
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	hanges from Original (February 2020) to Revision A	Page
•	Added D Package to data sheet	1
•	Added D package information to Pin Configuration and Functions	3
•	Added D package column to Thermal Information table	4

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5 Pin Configuration and Functions



Pin Functions

PIN		1/0	DESCRIPTION				
NAME	NO.	I/O	DESCRIPTION				
2A	1	Input	Channel 2, Input A				
2B	2	Input	Channel 2, Input B				
1A	3	Input	Channel 1, Input A				
1B	4	Input	Channel 1, Input B				
1C	5	Input	Channel 1, Input C				
1Y	6	Output	Channel 1, Output Y				
GND	7	_	Ground				
2C	8	Input	Channel 2, Input C				
2Y	9	Output	Channel 2, Output Y				
3Y	10	Output	Channel 3, Output Y				
ЗА	11	Input	Channel 3, Input A				
3B	12	Input	Channel 3, Input B				
3C	13	Input	Channel 3, Input C				
V _{CC}	14	_	Positive Supply				



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V_{CC}	Supply voltage		-0.5	7	V
I _{IK}	Input clamp current (2)	$V_{I} < -0.5 \text{ or } V_{I} > V_{CC} + 0.5$		±20	mA
I _{OK}	Output clamp current ⁽²⁾	V_{O} < -0.5 or V_{O} > V_{CC} + 0.5		±20	mA
Io	Continuous output current	$V_O = 0$ to V_{CC}		±35	mA
	Continuous current through V _{CC} or GND			±70	mA
TJ	Junction temperature (3)		150	°C	
T _{stg}	Storage temperature	-65	150	°C	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD) Electrosta		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	
	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1500	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MAX	UNIT
V _{CC}	Supply voltage	2	6	V
VI	Input voltage	0	V _{cc}	V
Vo	Output voltage	0	V _{CC}	V
Δt/Δν	Input transition rise and fall rate		Unlimited	ns/V
T _A	Ambient temperature	-40	125	°C

6.4 Thermal Information

		SN74H0	SN74HCS4075			
	THERMAL METRIC	PW (TSSOP)	D (SOIC)	UNIT		
		14 PINS	14 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance	151.7	133.6	°C/W		
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	79.4	89.0	°C/W		
$R_{\theta JB}$	Junction-to-board thermal resistance	94.7	89.5	°C/W		
Ψ_{JT}	Junction-to-top characterization parameter	25.2	45.5	°C/W		
Ψ_{JB}	Junction-to-board characterization parameter	94.1	89.1	°C/W		
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W		

⁽²⁾ The input and output voltage ratings may be exceeded if the input and output current ratings are observed. Do not exceed the absolute maximum voltage supply rating.

⁽³⁾ Guaranteed by design.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.5 Electrical Characteristics

over operating free-air temperature range; typical ratings measured at TA = 25°C (unless otherwise noted).

	PARAMETER	TEST CO	NDITIONS	V _{CC}	MIN	TYP	MAX	UNIT
				2 V	0.7		1.5	
V_{T+}	Positive switching threshold			4.5 V	1.7		3.15	V
				6 V	2.1		4.2	
				2 V	0.3		1.0	
V _{T-}	Negative switching threshold			4.5 V	0.9		2.2	V
				6 V	1.2		3.0	
				2 V	0.2		1.0	
ΔV_{T}	Hysteresis (V _{T+} - V _{T-})			4.5 V	0.4		1.4	V
				6 V	0.6		1.6	
			$I_{OH} = -20 \mu A$	2 V to 6 V	$V_{CC} - 0.1$	$V_{CC} - 0.002$		
V_{OH}	High-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -6 \text{ mA}$	4.5 V	4	4.3		V
			I_{OH} = -7.8 mA	6 V	5.4	5.75		
			$I_{OL} = 20 \mu A$	2 V to 6 V		0.002	0.1	
V_{OL}	Low-level output voltage	$V_I = V_{IH}$ or V_{IL}	$I_{OL} = 6 \text{ mA}$	4.5 V		0.18	0.30	V
			$I_{OL} = 7.8 \text{ mA}$	6 V		0.22	0.33	
I	Input leakage current	$V_I = V_{CC}$ or 0		6 V		±100	±1000	nA
I _{CC}	Supply current	$V_I = V_{CC}$ or 0, I_C	0 = 0	6 V		0.1	2	μΑ
Ci	Input capacitance			2 V to 6 V			5	pF
C _{pd}	Power dissipation capacitance per gate	No load		2 V to 6 V		10		pF

6.6 Switching Characteristics

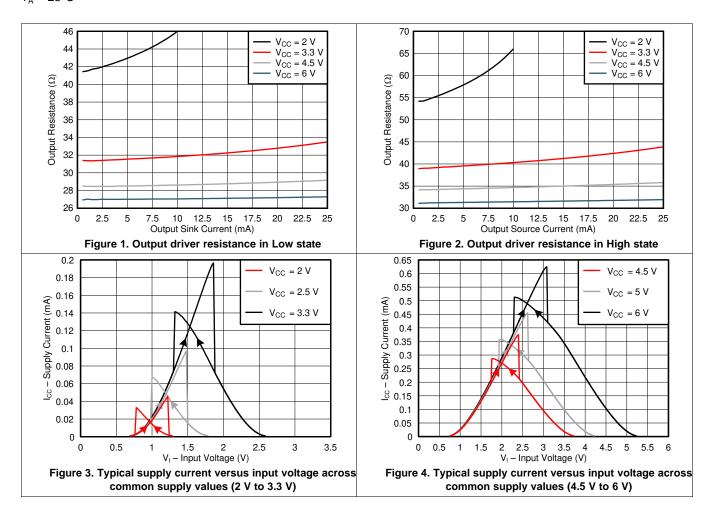
over operating free-air temperature range; typical ratings measured at TA = 25°C (unless otherwise noted). See the Parameter Measurement Information.

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC}	MIN	TYP	MAX	UNIT
t _{pd}	Propagation delay			2 V		13	32	
		A or B or C	Υ	4.5 V		6	15	ns
				6 V		5	12	
	Transition-time		Y	2 V		9	17	
t _t				4.5 V		5	8	ns
				6 V		4	7	

TEXAS INSTRUMENTS

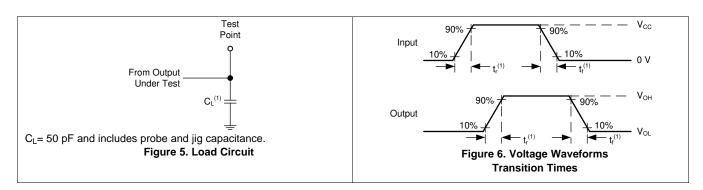
6.7 Typical Characteristics

 $T_A = 25^{\circ}C$



7 Parameter Measurement Information

- Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_O = 50 \Omega$, $t_t < 2.5 \text{ ns}$.
- The outputs are measured one at a time, with one input transition per measurement.

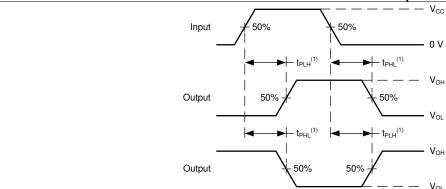


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Parameter Measurement Information (continued)



The maximum between t_{PLH} and T_{PHL} is used for $t_{\text{pd}}.$

Figure 7. Voltage Waveforms Propagation Delays

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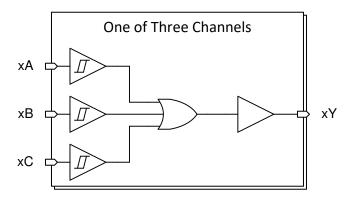


8 Detailed Description

8.1 Overview

This device contains three independent 3-input OR Gates with Schmitt-trigger inputs. Each gate performs the Boolean function Y = A + B + C in positive logic.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Balanced CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

8.3.2 CMOS Schmitt-Trigger Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using ohm's law $(R = V \div I)$.

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics*, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs slowly will also increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see Understanding Schmitt Triggers.

8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in Figure 8.

CAUTION

Voltages beyond the values specified in the Absolute Maximum Ratings table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

Product Folder Links: SN74HCS4075

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Feature Description (continued)

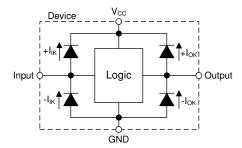


Figure 8. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

Table 1. Function Table

	OUTPUT		
Α	В	С	Y
L	L	L	L
Н	Х	X	Н
X	Н	X	Н
Х	Х	Н	Н



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74HCS4075 includes three 3-input OR gates with Schmitt-trigger inputs. These 3-input OR gates work independently, but can be combined to get up to a 7-input OR gate. It can be used with all three inputs active, or one input can be disabled by directly connecting it to ground to turn the device into a 2-input OR gate.

The SN74HCS4075 is used to directly control the Enable pin of a fan driver. The fan driver requires only one input signal to be HIGH before being enabled, and should be disabled in the event that all signals go LOW. The 3-input OR gate function combines the three individual overheat signals into a single active-high enable signal.

Temperature sensors can often be spread throughout a system rather than being in a centralized location. This would mean longer length traces or wires to pass signals through leading to slower edge transitions. This makes the SN74HCS4075 ideal for the application since it has Schmitt-trigger inputs that do not have input transition rate requirements.

9.2 Typical Application

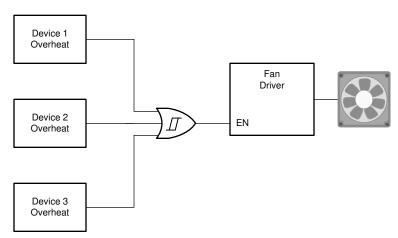


Figure 9. Typical application block diagram

9.2.1 Design Requirements

- All signals in the system operate at 5 V
- The fan driver should be enabled if any one or more of these conditions apply:
 - Device 1 overheats
 - Device 2 overheats
 - Device 3 overheats

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HCS4075 plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*. The logic device can only source or sink as much current as it is provided at the supply and ground pins, respectively. Be sure not to exceed the maximum total current through GND or V_{CC} listed in the *Absolute Maximum Ratings*.



Typical Application (continued)

The SN74HCS4075 can drive a load with a total capacitance less than or equal to 50 pF connected to a high-impedance CMOS input while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 70 pF.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and C_{pd} Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

CAUTION

The maximum junction temperature, T_J(max) listed in the *Absolute Maximum Ratings*, is an *additional limitation* to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{t-}(min)$ to be considered a logic LOW, and $V_{t+}(max)$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HCS4075, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

The SN74HCS4075 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the ΔV_T (min) in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the Feature Description for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. Similarly, the ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*. The plots in and provide a typical relationship between output voltage and current for this device.

Unused outputs can be left floating.

Refer to Feature Description for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

- 1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout*.
- 2. Ensure the capacitive load at the output is ≤ 70 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCS4075 to the receiving device.
- 3. Ensure the resistive load at the output is larger than $(V_{CC} / 25 \text{ mA}) \Omega$. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load



Typical Application (continued)

measured in megaohms; much larger than the minimum calculated above.

4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation

9.2.3 Application Curves

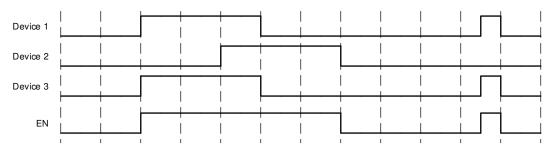


Figure 10. Application timing diagram

Product Folder Links: SN74HCS4075

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10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in *Figure 11*.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

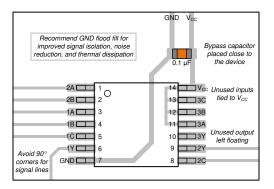


Figure 11. Example layout for the SN74HCS4075



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- HCMOS Design Considerations
- CMOS Power Consumption and CPD Calculation
- Designing with Logic

12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

12.3 Community Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
SN74HCS4075DR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	HCS4075
SN74HCS4075DR.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS4075
SN74HCS4075PWR	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	HCS4075
SN74HCS4075PWR.A	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS4075
SN74HCS4075PWRG4	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS4075
SN74HCS4075PWRG4.A	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS4075

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

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OTHER QUALIFIED VERSIONS OF SN74HCS4075:

Automotive: SN74HCS4075-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCS4075DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HCS4075PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74HCS4075PWRG4	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCS4075DR	SOIC	D	14	2500	353.0	353.0	32.0
SN74HCS4075PWR	TSSOP	PW	14	2000	353.0	353.0	32.0
SN74HCS4075PWRG4	TSSOP	PW	14	2000	353.0	353.0	32.0



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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